



IRL2703PBF Information

Part Number IRL2703PBF

Manufacturer Infineon Technologies

Category Discrete Semiconductor Products

Transistors - FETs, MOSFETs - Single

Description MOSFET N-CH 30V 24A TO-220AB

Package TO-220-3

For the pricing/inventory/lead time, please contact

Website: https://www.heisener.com For Reference Only

E-mail: salesdept@heisener.com



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IRL2703PBF Specifications

| Manufacturer Part NumberIRL2703PBFManufacturerInfineon TechnologiesCategoryDiscrete Semiconductor ProductsTransistors - FETs, MOSFETs - SinglePackageTO-220-3SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250µAGate Charge (Qg) (Max) @ Vgs15nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220ABReport errors? | | |
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| Category Discrete Semiconductor Products Package TO-220-3 Series HEXFET? FET Type N-Channel Technology MOSFET (Metal Oxide) Drain to Source Voltage (Vdss) 30V Current - Continuous Drain (Id) @ 25°C 24A (Tc) Drive Voltage (Max Rds On, Min Rds On) 4.5V, 10V Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds 450pF @ 25V Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Manufacturer Part Number | IRL2703PBF |
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| SeriesHEXFET?FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250µAGate Charge (Qg) (Max) @ Vgs15nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | | Transistors - FETs, MOSFETs - Single |
| FET TypeN-ChannelTechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Package | TO-220-3 |
| TechnologyMOSFET (Metal Oxide)Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | Series | HEXFET? |
| Drain to Source Voltage (Vdss)30VCurrent - Continuous Drain (Id) @ 25°C24A (Tc)Drive Voltage (Max Rds On, Min Rds On)4.5V, 10VVgs(th) (Max) @ Id1V @ 250μAGate Charge (Qg) (Max) @ Vgs15nC @ 4.5VInput Capacitance (Ciss) (Max) @ Vds450pF @ 25VVgs (Max)±16VFET Feature-Power Dissipation (Max)45W (Tc)Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | FET Type | N-Channel |
| Current - Continuous Drain (Id) @ 25°C Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 45W (Tc) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature Supplier Device Package Package / Case TO-220AB TO-220AB | Technology | MOSFET (Metal Oxide) |
| Drive Voltage (Max Rds On, Min Rds On) Vgs(th) (Max) @ Id 1V @ 250μA Gate Charge (Qg) (Max) @ Vgs 15nC @ 4.5V Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB | Drain to Source Voltage (Vdss) | 30V |
| Vgs(th) (Max) @ Id Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs Operating Temperature Supplier Device Package Package / Case 15nC @ 4.5V 450pF @ 25V 450pF @ 25V | Current - Continuous Drain (Id) @ 25°C | 24A (Tc) |
| Gate Charge (Qg) (Max) @ Vgs Input Capacitance (Ciss) (Max) @ Vds 450pF @ 25V Vgs (Max) ±16V FET Feature Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package Package / Case TO-220AB TO-220-3 | Drive Voltage (Max Rds On, Min Rds On) | 4.5V, 10V |
| Input Capacitance (Ciss) (Max) @ Vds Vgs (Max) ±16V FET Feature - Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs(th) (Max) @ Id | 1V @ 250μA |
| Vgs (Max) ±16V FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Gate Charge (Qg) (Max) @ Vgs | 15nC @ 4.5V |
| FET Feature - Power Dissipation (Max) 45W (Tc) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Input Capacitance (Ciss) (Max) @ Vds | 450pF @ 25V |
| Power Dissipation (Max) Rds On (Max) @ Id, Vgs 40 mOhm @ 14A, 10V Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Vgs (Max) | ±16V |
| Rds On (Max) @ Id, Vgs40 mOhm @ 14A, 10VOperating Temperature-55°C ~ 175°C (TJ)Mounting TypeThrough HoleSupplier Device PackageTO-220ABPackage / CaseTO-220-3 | FET Feature | - |
| Operating Temperature -55°C ~ 175°C (TJ) Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Power Dissipation (Max) | 45W (Tc) |
| Mounting Type Through Hole Supplier Device Package TO-220AB Package / Case TO-220-3 | Rds On (Max) @ Id, Vgs | 40 mOhm @ 14A, 10V |
| Supplier Device Package TO-220AB Package / Case TO-220-3 | Operating Temperature | -55°C ~ 175°C (TJ) |
| Package / Case TO-220-3 | Mounting Type | Through Hole |
| | Supplier Device Package | TO-220AB |
| Report errors? | Package / Case | TO-220-3 |
| | | Report errors? |

IRL2703PBF Guarantees



Quality Guarantees

We provide 90 days warranty. *

If the items you received were not in perfect quality, we would be responsible for your refund or replacement, but the items must be returned in their original condition.



Service Guarantees

We guarantee 100% customer satisfaction.

Our experienced sales team and tech support team back our services to satisfy all our customers.

IRL2703PBF Payment Methods



















IRL2703PBF Shipping Methods













If you have any question about IRL2703PBF, please do not hesitate to contact us!

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